

**Amendments to the Specification:**

Please replace the paragraph beginning at line 19 on page 10 with the following amended paragraph:

The substrate having the second species monolayer and the reaction product is exposed to a third gaseous substance different from the first and second precursors effective to selectively remove the reaction product from the substrate relative to the second species monolayer. With respect to the exemplary depicted hafnium oxide being formed, Fig. 3 illustrates exposure of the Fig. 2 substrate to such a third gaseous substance which has selectively removed the  $\text{SiO}_x$  from the substrate relative to the remaining  $\text{HfO}_x$ . Exemplary preferred third gaseous substances to effect such selective removing includes include fluorine comprising gases. Further, an example includes a halide, for example a hydrogen halide such as HF. Alternate exemplary gases include  $\text{F}_2$  and  $\text{CHF}_4$ , by way of example only. Such materials are also believed to be suitably usable in etching silicon dioxide selectively relative to  $\text{Al}_2\text{O}_3$ . In the context of this document, "selective removal" refers to a removal rate of the material being removed at a rate of at least 2:1 to the material remaining.